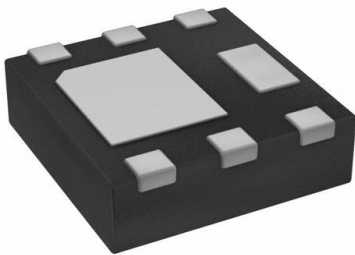


# DMN2024UFDF-7 Datasheet

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|                              |  |
|------------------------------|--|
| DiGi Electronics Part Number | DMN2024UFDF-7-DG   |
| Manufacturer                 | <a href="#">Diodes Incorporated</a>                                    |
| Manufacturer Product Number  | DMN2024UFDF-7  |
| Description                  | MOSFET N-CH 20V 7.1A 6UDFN   |
| Detailed Description         | N-Channel 20 V 7.1A (Ta) 960mW (Ta) Surface Mount U-DFN2020-6 (Type F) |



Tel: +00 852-30501935

RFQ Email: [Info@DiGi-Electronics.com](mailto:Info@DiGi-Electronics.com)

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## Purchase and inquiry

Manufacturer Product Number:

DMN2024UFD-7

Series:

-

FET Type:

N-Channel

Drain to Source Voltage (V<sub>dss</sub>):

20 V

Drive Voltage (Max R<sub>ds On</sub>, Min R<sub>ds On</sub>):

1.5V, 4.5V

V<sub>gs(th)</sub> (Max) @ I<sub>d</sub>:

1V @ 250μA

V<sub>gs</sub> (Max):

±10V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (T<sub>J</sub>)

Supplier Device Package:

U-DFN2020-6 (Type F)

Base Product Number:

DMN2024

Manufacturer:

Diodes Incorporated

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (I<sub>d</sub>) @ 25°C:

7.1A (T<sub>a</sub>)

R<sub>ds On</sub> (Max) @ I<sub>d</sub>, V<sub>gs</sub>:

22mΩ @ 4A, 4.5V

Gate Charge (Q<sub>g</sub>) (Max) @ V<sub>gs</sub>:

0.9 nC @ 10 V

Input Capacitance (C<sub>iss</sub>) (Max) @ V<sub>ds</sub>:

647 pF @ 10 V

Power Dissipation (Max):

960mW (T<sub>a</sub>)

Mounting Type:

Surface Mount

Package / Case:

6-UDFN Exposed Pad

## Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99



DMN2024UFDF

## 20V N-CANNEL ENHANCEMENT MODE MOSFET

## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> Max       | I <sub>D</sub> Max<br>T <sub>A</sub> = +25°C |
|-------------------|-------------------------------|--|
| 20V               | 22mΩ @ V <sub>GS</sub> = 4.5V | 7.1A   |
|                   | 26mΩ @ V <sub>GS</sub> = 2.5V | 6.5A   |
|                   | 36mΩ @ V <sub>GS</sub> = 1.8V | 5.5A   |
|                   | 50mΩ @ V <sub>GS</sub> = 1.5V | 4.7A   |

## Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

## Applications

- Battery Management Application
- Power Management Functions
- DC-DC Converters

## Features

- 0.6mm Profile—Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

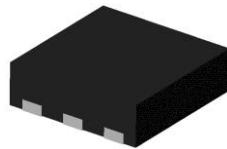
## Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0065 grams (Approximate)

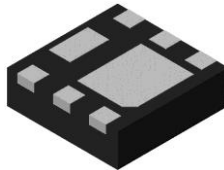
U-DFN2020-6 (Type F)



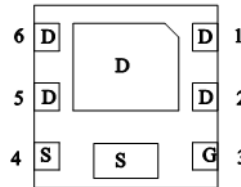
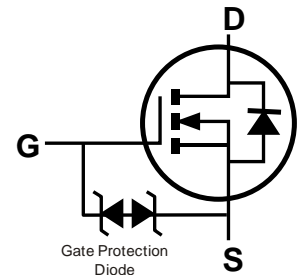
ESD PROTECTED



Top View



Bottom View

Pin Out  
Bottom View

Internal Schematic

## Ordering Information (Note 4)

| Part Number    | Reel Size (inches) | Quantity Per Reel |
|----------------|--------------------|-------------------|
| DMN2024UFDF-7  | 7                  | 3,000             |
| DMN2024UFDF-13 | 13                 | 10,000            |

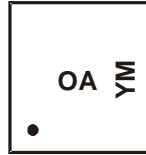
- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.



DMN2024UFD

## Marking Information

Site1



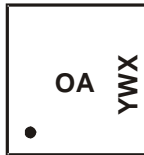
OA = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: H = 2020)  
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 |
|------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code | F    | G    | H    | I    | J    | K    | L    | M    | N    | O    | P    | R    |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

Site 2



OA = Product Type Marking Code  
 YWX = Date Code Marking  
 Y = Year (ex: 0 = 2020)  
 W = Week (ex: a = Week 27; z Represents Week 52 and 53)  
 X = Internal Code (ex: U = Monday)

Date Code Key

| Year | 2018 | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 |
|------|------|------|------|------|------|------|------|------|------|------|------|------|
| Code | 8    | 9    | 0    | 1    | 2    | 3    | 4    | 5    | 6    | 7    | 8    | 9    |

| Week | 1-26 | 27-52 | 53 |
|------|------|-------|----|
| Code | A-Z  | a-z   | z  |

| Internal Code | Sun | Mon | Tue | Wed | Thu | Fri | Sat |
|---------------|-----|-----|-----|-----|-----|-----|-----|
| Code          | T   | U   | V   | W   | X   | Y   | Z   |



DMN2024UFD

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   |              |                        | Symbol           | Value | Unit |
|--|--------------|------------------------|------------------|-------|------|
| Drain-Source Voltage                                     |              |                        | V <sub>DSS</sub> | 20    | V    |
| Gate-Source Voltage                                      |              |                        | V <sub>GSS</sub> | ±10   | V    |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V | Steady State | T <sub>A</sub> = +25°C | I <sub>D</sub>   | 7.1   | A    |
|  |              | T <sub>A</sub> = +70°C |                  | 5.6   |      |
| Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)       |              |                        | I <sub>DM</sub>  | 40    | A    |
| Continuous Source-Drain Diode Current                    |              |                        | I <sub>S</sub>   | 2.6   | A    |
| Avalanche Current (Note 7) L = 0.1mH                     |              |                        | I <sub>AS</sub>  | 12    | A    |
| Avalanche Energy (Note 7) L = 0.1mH                      |              |                        | E <sub>AS</sub>  | 8     | mJ   |

## Thermal Characteristics

| Characteristic                                   |                        | Symbol                            | Value       | Unit |
|--|------------------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 5)                 | T <sub>A</sub> = +25°C | P <sub>D</sub>                    | 0.96        | W    |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State           | R <sub>θJA</sub>                  | 130         | °C/W |
| Total Power Dissipation (Note 6)                 | T <sub>A</sub> = +25°C | P <sub>D</sub>                    | 1.67        | W    |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State           | R <sub>θJA</sub>                  | 75          | °C/W |
| Thermal Resistance, Junction to Case (Note 6)    |                        | R <sub>θJC</sub>                  | 16          |      |
| Operating and Storage Temperature Range          |                        | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol              | Min | Typ  | Max | Unit | Test Condition  |
|--|---------------------|-----|------|-----|------|---|
| <b>OFF CHARACTERISTICS (Note 8)</b>                    |                     |     |      |     |      |   |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | 20  | —    | —   | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA  |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>    | —   | —    | 1   | μA   | V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V   |
| Gate-Source Leakage                                    | I <sub>GSS</sub>    | —   | —    | ±10 | μA   | V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V   |
| <b>ON CHARACTERISTICS (Note 8)</b>                     |                     |     |      |     |      |   |
| Gate Threshold Voltage                                 | V <sub>GS(TH)</sub> | 0.5 | —    | 1.0 | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA  |
| Static Drain-Source On-Resistance                      | R <sub>DS(ON)</sub> | —   | 15   | 22  | mΩ   | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4A   |
|  |                     |     | 17   | 26  |      | V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 4A   |
|  |                     |     | 20   | 36  |      | V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 4A   |
|  |                     |     | 23   | 50  |      | V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 4A   |
| Diode Forward Voltage                                  | V <sub>SD</sub>     | —   | 0.7  | 1.0 | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 5A   |
| <b>DYNAMIC CHARACTERISTICS (Note 9)</b>                |                     |     |      |     |      |   |
| Input Capacitance                                      | C <sub>ISS</sub>    | —   | 647  | —   | pF   | V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz   |
| Output Capacitance                                     | C <sub>OSS</sub>    | —   | 78   | —   |      |   |
| Reverse Transfer Capacitance                           | C <sub>RSS</sub>    | —   | 38   | —   |      |   |
| Gate Resistance  | R <sub>G</sub>      | —   | 400  | —   | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz  |
| Total Gate Charge (V <sub>GS</sub> = 4.5V)             | Q <sub>G</sub>      | —   | 6.5  | —   | nC   | V <sub>DS</sub> = 10V, I <sub>D</sub> = 6.5A  |
| Total Gate Charge (V <sub>GS</sub> = 10V)              | Q <sub>G</sub>      | —   | 14.8 | —   |      |   |
| Gate-Source Charge                                     | Q <sub>GS</sub>     | —   | 1.1  | —   |      |   |
| Gate-Drain Charge                                      | Q <sub>GD</sub>     | —   | 1.7  | —   |      |   |
| Turn-On Delay Time                                     | t <sub>D(ON)</sub>  | —   | 98   | —   | ns   | V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 6Ω, R <sub>L</sub> = 10Ω, I <sub>D</sub> = 1A |
| Turn-On Rise Time                                      | t <sub>R</sub>      | —   | 140  | —   |      |   |
| Turn-Off Delay Time                                    | t <sub>D(OFF)</sub> | —   | 1024 | —   |      |   |
| Turn-Off Fall Time                                     | t <sub>F</sub>      | —   | 434  | —   |      |   |
| Reverse Recovery Time                                  | t <sub>RR</sub>     | —   | 245  | —   | ns   | I <sub>F</sub> = 1A, di/dt = 100A/μs  |
| Reverse Recovery Charge                                | Q <sub>RR</sub>     | —   | 149  | —   | nC   | I <sub>F</sub> = 1A, di/dt = 100A/μs  |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



DMN2024UFDF

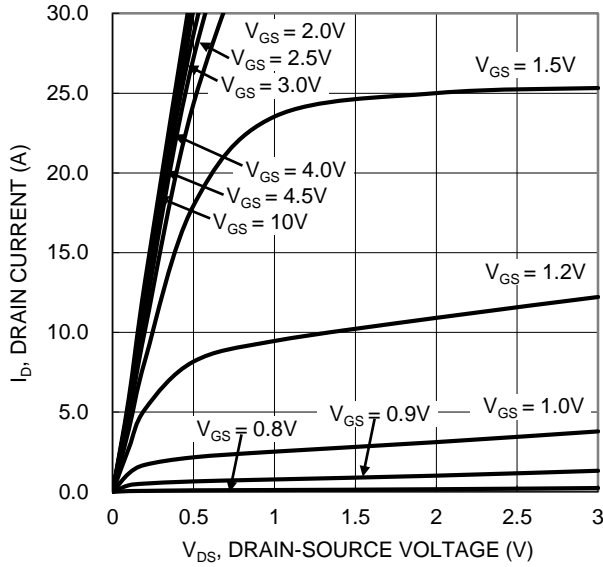


Figure 1. Typical Output Characteristic

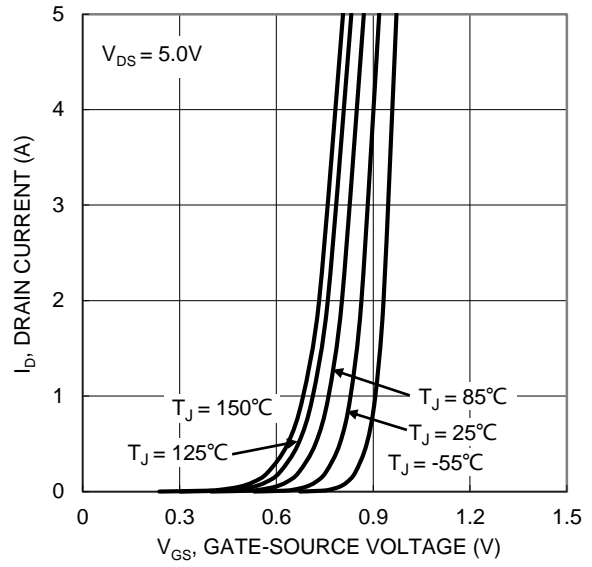


Figure 2. Typical Transfer Characteristic

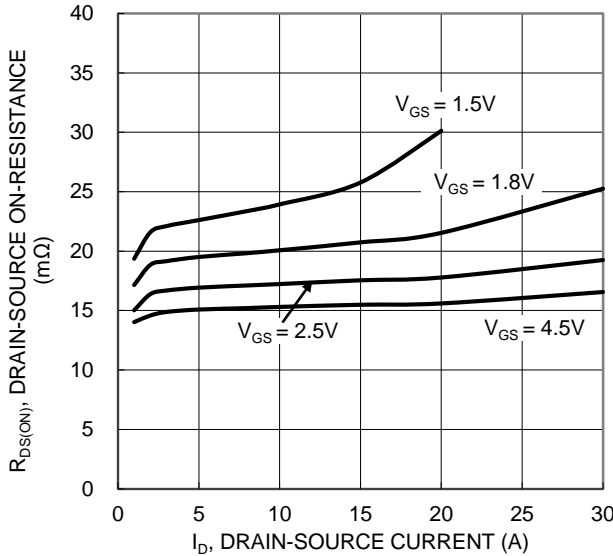


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

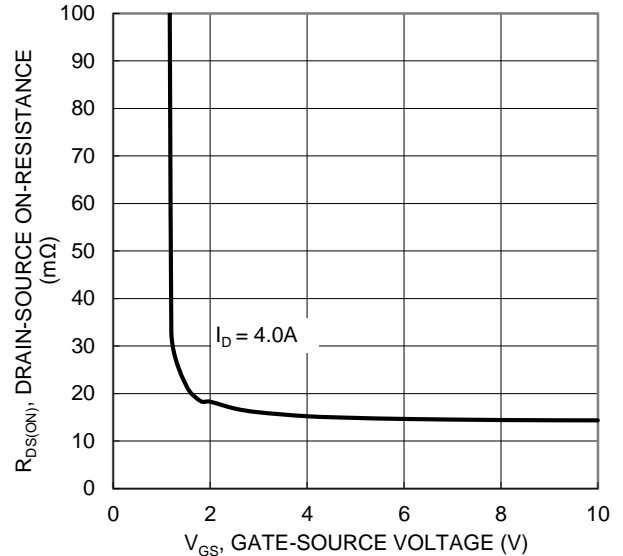


Figure 4. Typical Transfer Characteristic

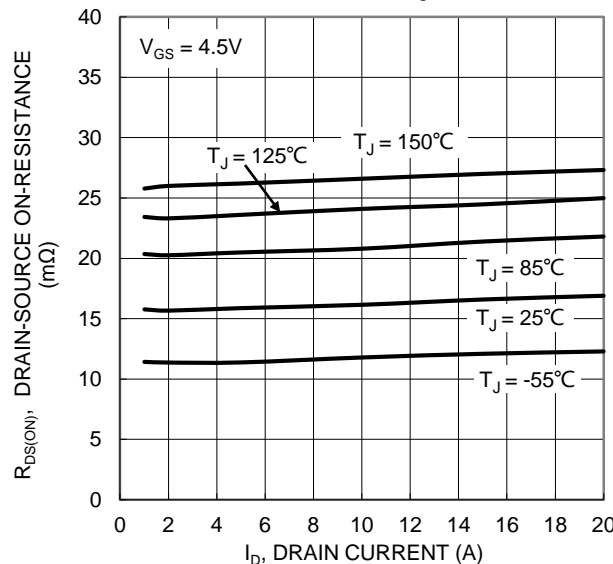


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

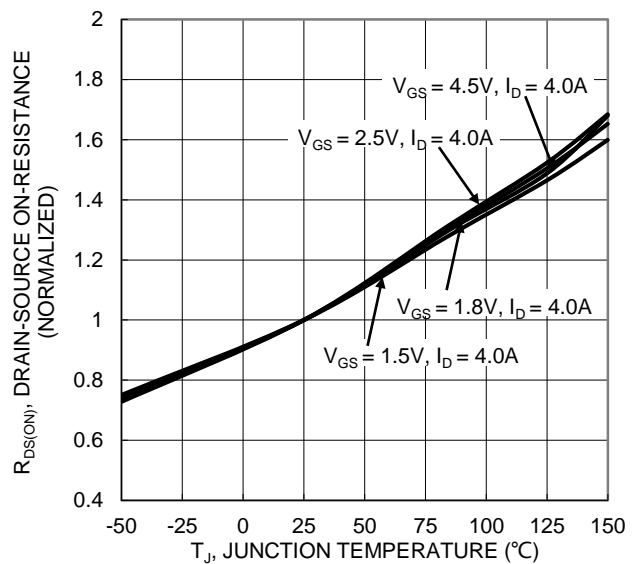


Figure 6. On-Resistance Variation with Temperature



**DMN2024UFDF**

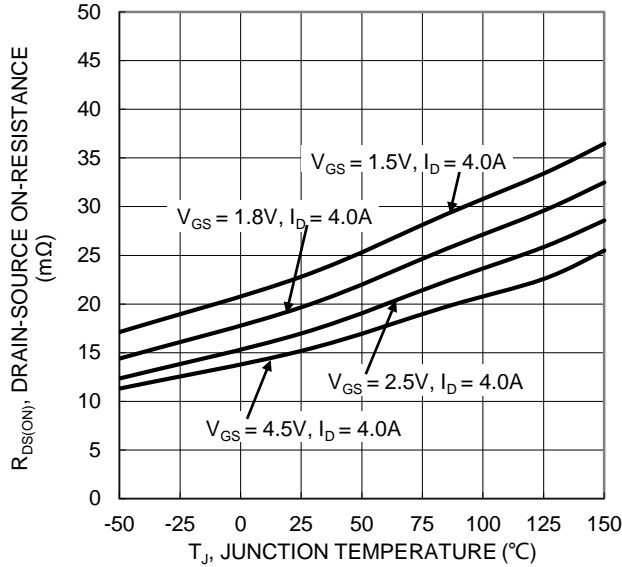


Figure 7. On-Resistance Variation with Temperature

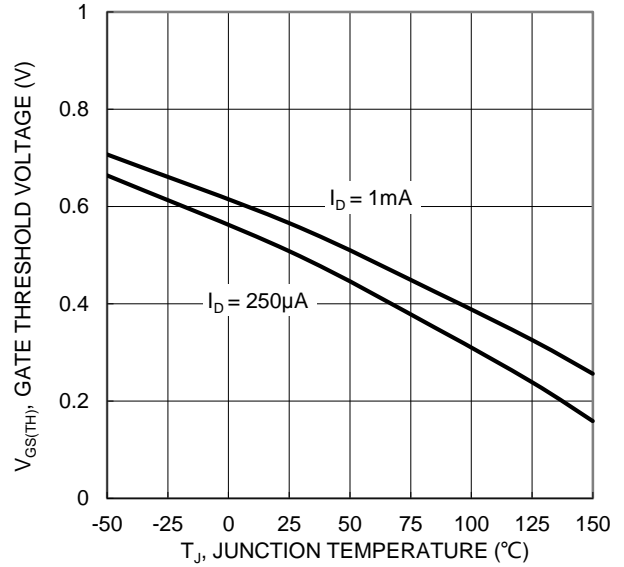


Figure 8. Gate Threshold Variation vs. Junction Temperature

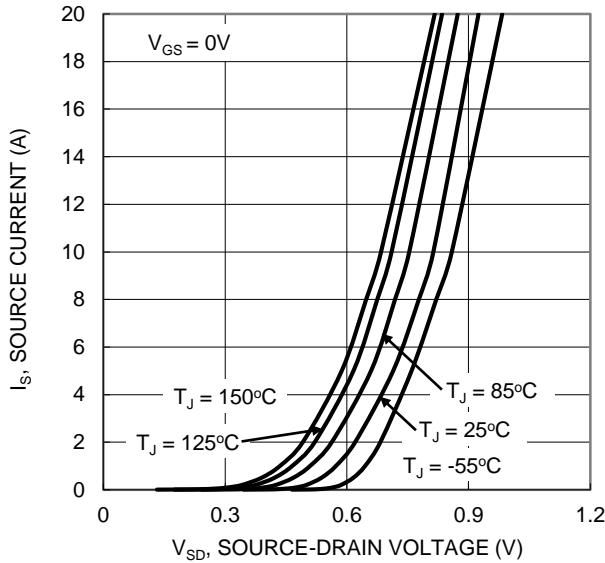


Figure 9. Diode Forward Voltage vs. Current

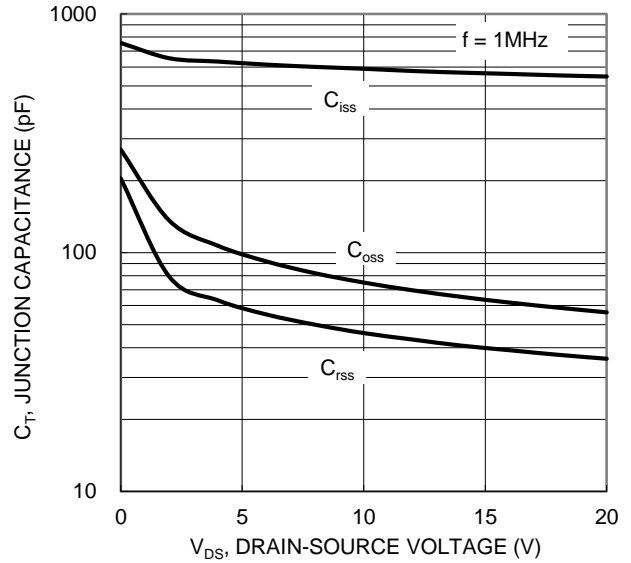


Figure 10. Typical Junction Capacitance

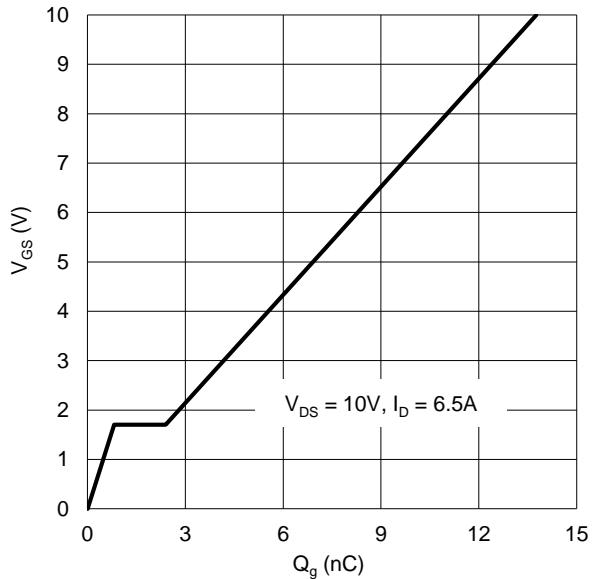


Figure 11. Gate Charge

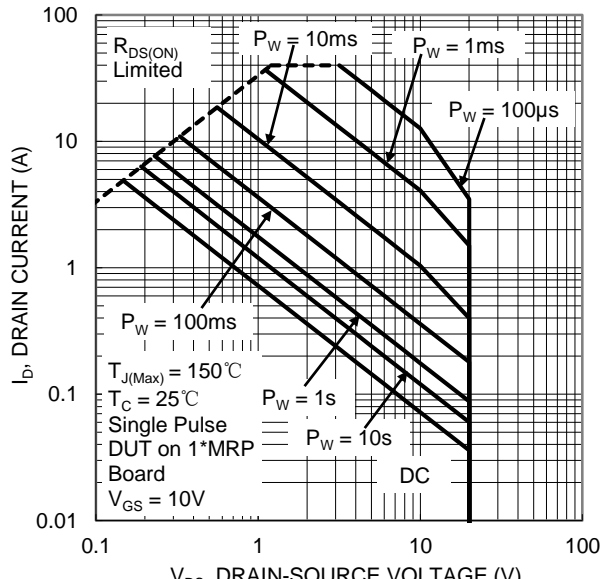


Figure 12. SOA, Safe Operation Area



DMN2024UFD

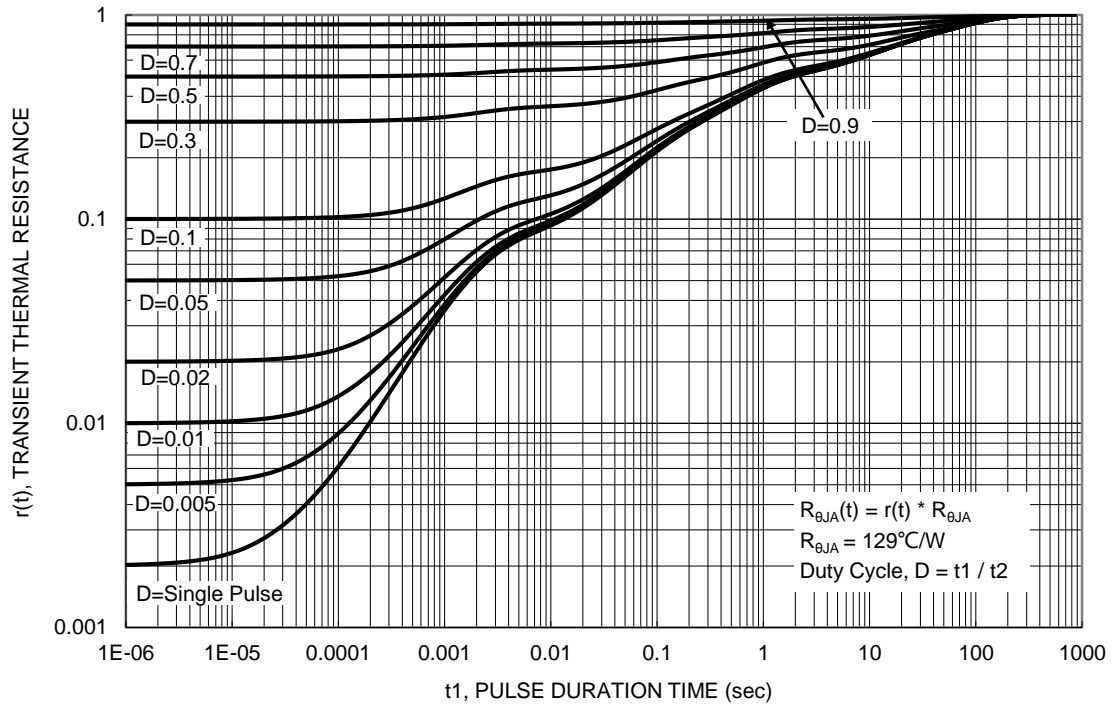


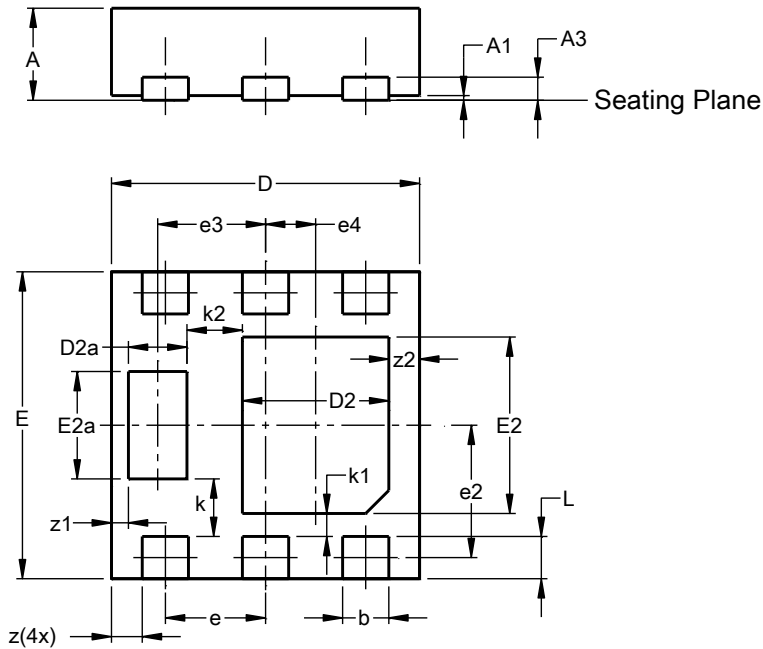
Figure 13. Transient Thermal Resistance



## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

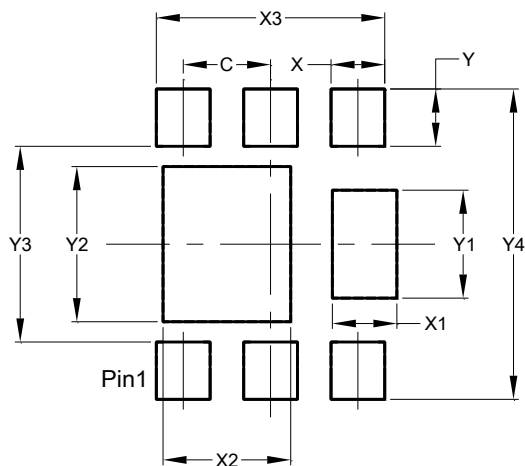


| U-DFN2020-6<br>(Type F) |           |       |       |
|-------------------------|-----------|-------|-------|
| Dim                     | Min       | Max   | Typ   |
| A                       | 0.57      | 0.63  | 0.60  |
| A1                      | 0.00      | 0.05  | 0.03  |
| A3                      | -         | -     | 0.15  |
| b                       | 0.25      | 0.35  | 0.30  |
| D                       | 1.95      | 2.05  | 2.00  |
| D2                      | 0.85      | 1.05  | 0.95  |
| D2a                     | 0.33      | 0.43  | 0.38  |
| E                       | 1.95      | 2.05  | 2.00  |
| E2                      | 1.05      | 1.25  | 1.15  |
| E2a                     | 0.65      | 0.75  | 0.70  |
| e                       | 0.65 BSC  |       |       |
| e2                      | 0.863 BSC |       |       |
| e3                      | 0.70 BSC  |       |       |
| e4                      | 0.325 BSC |       |       |
| k                       | 0.37 BSC  |       |       |
| k1                      | 0.15 BSC  |       |       |
| k2                      | 0.36 BSC  |       |       |
| L                       | 0.225     | 0.325 | 0.275 |
| z                       | 0.20 BSC  |       |       |
| z1                      | 0.110 BSC |       |       |
| z2                      | 0.20 BSC  |       |       |
| All Dimensions in mm    |           |       |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



| Dimensions | Value<br>(in mm) |
|------------|------------------|
| C          | 0.650            |
| X          | 0.400            |
| X1         | 0.480            |
| X2         | 0.950            |
| X3         | 1.700            |
| Y          | 0.425            |
| Y1         | 0.800            |
| Y2         | 1.150            |
| Y3         | 1.450            |
| Y4         | 2.300            |



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2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.

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